



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **KANO, Takashi**

Serial No.: 09/532,775

Filed: **March 22, 2000**

Group Art Unit: 2828

Examiner: **Tuan M. Nguyen**

P.T.O. Confirmation No.: 8757

For: **SEMICONDUCTOR LASER DEVICE**

**AMENDMENT UNDER 37 CFR §1.111**

Commissioner for Patents  
Washington, D.C. 20231  
Sir:

January 18, 2003

In response to the Office Action dated **July 19, 2002**, extended to **January 19, 2003** a 3 month Petition for Extension of Time, please amend the above-identified application as follows:

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**IN THE CLAIMS:**

Please amend claims 1-3 as indicated below:

**1. (Amended)** A semiconductor laser device comprising:

a first nitride based semiconductor layer including a first conductivity type cladding layer and an active layer and containing at least one of boron, aluminum, gallium, indium and thallium;

A1 a current blocking layer, formed on said first nitride based semiconductor layer, having a striped opening; and